

**2SC2998**



2003A

NPN Epitaxial Planar Silicon Transistor

T-35-13

# High Speed Switching Applications

©922B

**Features**

- . Fast switching speed.
- . High breakdown voltage.

**Absolute Maximum Ratings at Ta=25°C**

		unit
Collector to Base Voltage	V <sub>CB0</sub>	60 V
Collector to Emitter Voltage	V <sub>CE0</sub>	50 V
Emitter to Base Voltage	V <sub>EBO</sub>	5 V
Collector Current	I <sub>C</sub>	150 mA
Peak Collector Current	i <sub>cp</sub>	400 mA
Collector Dissipation	P <sub>C</sub>	500 mW
Junction Temperature	T <sub>J</sub>	150 °C
Storage Temperature	T <sub>stg</sub>	-55 to +150 °C

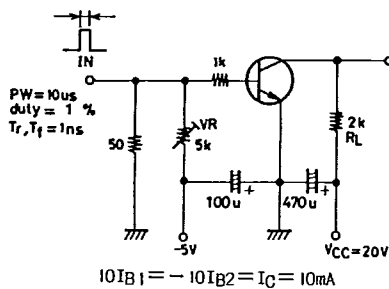
**Electrical Characteristics at Ta=25°C**

			min	typ	max	unit
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> =40V, I <sub>E</sub> =0			0.1	uA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =4V, I <sub>C</sub> =0			0.1	uA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =6V, I <sub>C</sub> =1mA	100*		560*	
Gain Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> =6V, I <sub>C</sub> =1mA		100		MHz
Output Capacitance	c <sub>ob</sub>	V <sub>CB</sub> =6V, f=1MHz		2.7		pF
C-E Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA		0.1	0.4	V
B-E Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA		0.75	1.1	V
C-B Breakdown Voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =10uA, I <sub>E</sub> =0	60			V
C-E Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =1mA, R <sub>BE</sub> =∞	50			V
E-B Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =10uA, I <sub>C</sub> =0	5			V
Delay Time	t <sub>d</sub>	See specified Test Circuit.	40	60		ns
Rise Time	t <sub>r</sub>	" "	80	130		ns
Storage Time	t <sub>stg</sub>	" "	230	450		ns
Fall Time	t <sub>f</sub>	" "	160	250		ns

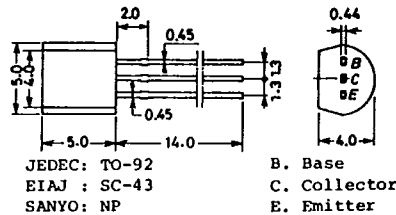
\*:The 2SC2998 is classified by h<sub>FE</sub> at 1mA.

100	E	200	160	F	320	280	G	560
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**Switching Time Test Circuit**

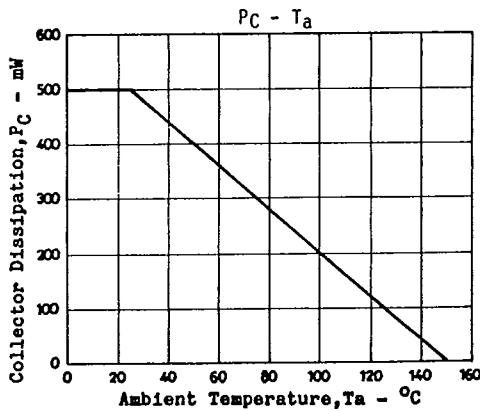
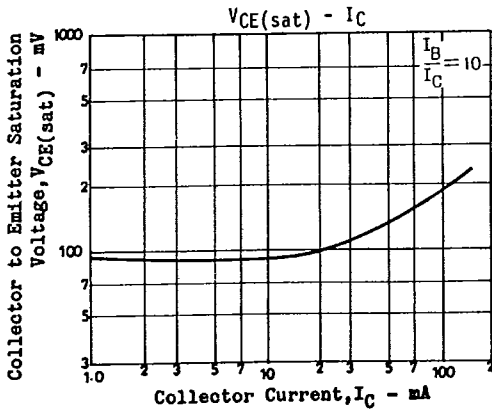
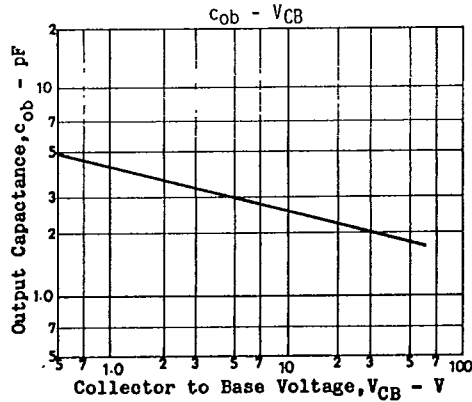
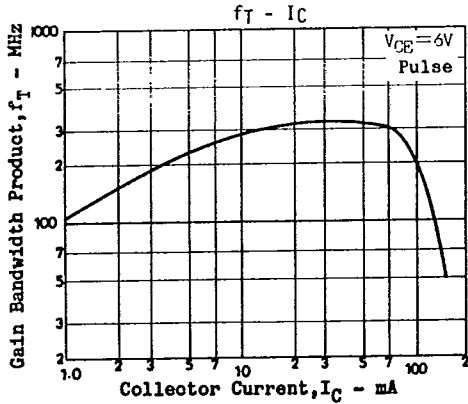
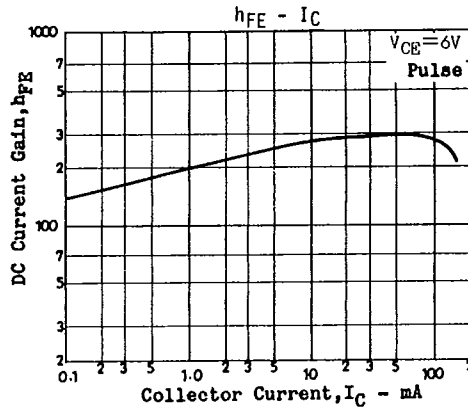
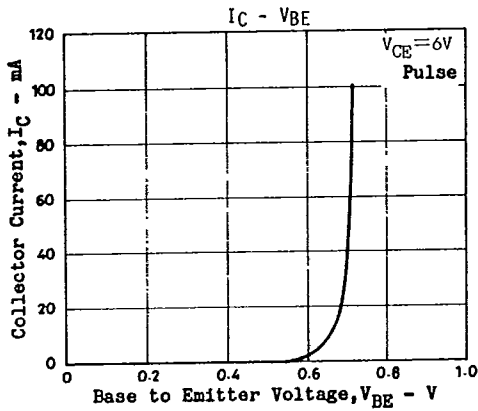
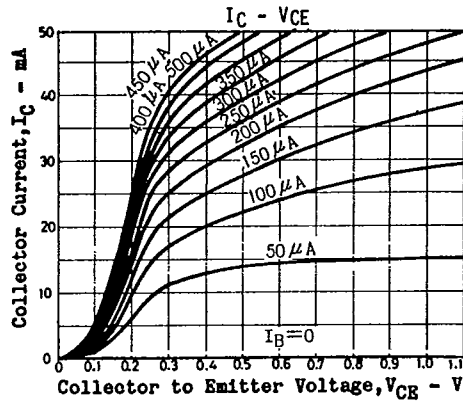
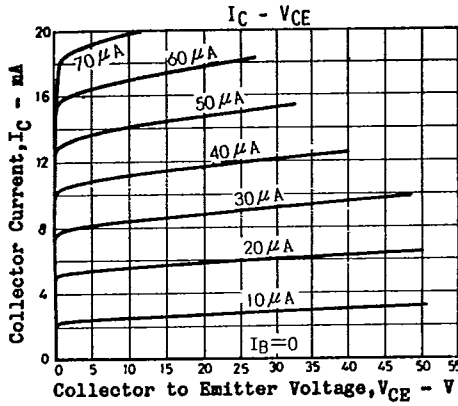


**Case Outline 2003A (unit:mm)**



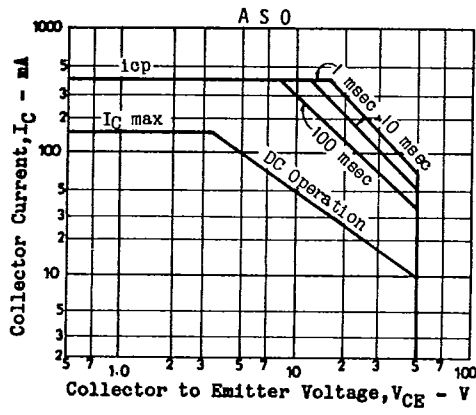
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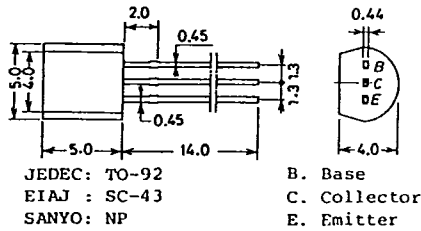
T-91-20

# CASE OUTLINES AND ATTACHMENTS

- All of Sanyo Transistor case outlines are illustrated below.
- All dimensions are in mm, and dimensions which are not followed by min. or max. are represented by typical values.
- No marking is indicated.

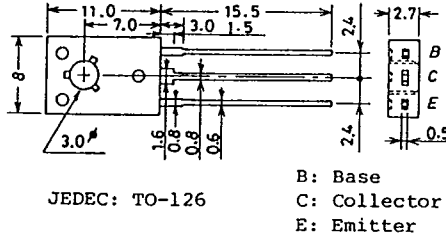
Case Outline-[2003A]

unit:mm



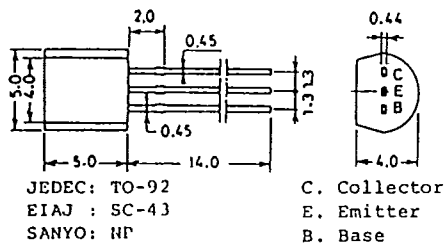
Case Outline-[2009A]

unit:mm



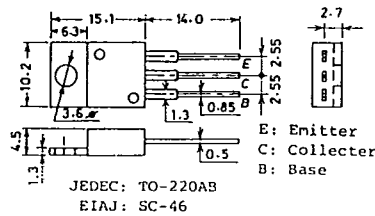
Case Outline-[2004A]

unit:mm



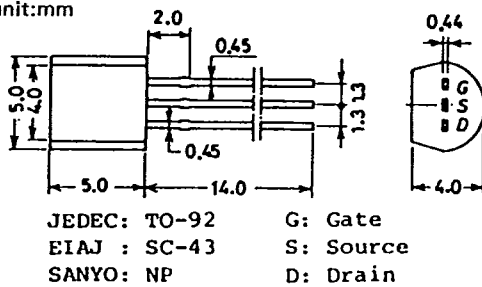
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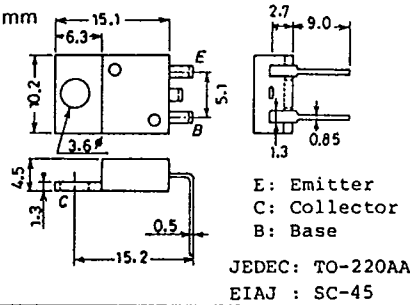
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unit:mm



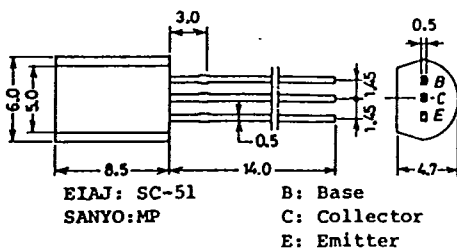
Case Outline-[2012]

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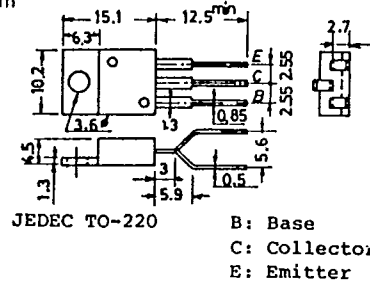
Case Outline-[2006A]

unit:mm



Case Outline-[2013]

unit:mm







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